4. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:

depositing a metal containing silicon or an alloy thereof on a bulk silicon substrate;

reacting said metal containing silicon or said alloy to form a first silicide phase;

etching any unreacted metal containing silicon or alloy;

depositing a silicon cap layer over said first silicide phase;

reacting the silicon cap layer to form a second silicide phase; and

etching any unreacted silicon from said silicon cap layer.

8. (Amended) The method of claim 4, wherein said reacting of said metal comprises performing a first rapid thermal anneal (RTA) to form a metal-silicon phase, such that the deposited metal containing silicon with the underlay Si, converts some of the Si into metal-Si,

wherein said etching comprises selectively etching any unreacted metal containing silicon, thereby leaving the metal-silicon regions intact,

wherein said depositing comprises performing a blanket deposition of a silicon film, and

wherein said reacting of said silicon cap comprises performing a second RTA to form a metal di-silicide.

10. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:

depositing a metal or an alloy thereof on a bulk silicon substrate;

reacting said metal or said alloy to form a first silicide phase;

etching any unreacted metal or alloy;

depositing a silicon cap layer over said first silicide phase;

reacting the silicon cap layer to form a second silicide phase; and

etching any unreacted silicon from said silicon cap layer,

wherein said metal is co-deposited with silicon.

Sub C4 B5

13. (Amended) A method for fabricating a silicide, said method comprising:

providing a substrate having a silicon layer;

depositing a metal containing silicon or an alloy over said silicon layer;

reacting said metal containing silicon or said alloy to form a first silicide phase;

etching any unreacted metal containing silicon or alloy; and

depositing a silicon cap layer over said metal containing silicon or said alloy;

reacting the silicon cap layer, to form a second silicide phase; and

etching any unreacted silicon from said silicon cap layer.

Sub C5 B6

25. (Amended) A method for fabricating a silicide for a semiconductor device, said method comprising:

depositing a metal or an alloy thereof on a silicon substrate;

reacting said metal or said alloy to form a first forming silicide phase;

etching any unreacted metal or alloy;

depositing a silicon cap layer over said first forming silicide phase;

reacting the silicon cap layer to form a second silicide phase, for said semiconductor device; and

etching any unreacted silicon from said silicon cap layer.

26. (Amended) A method for fabricating a silicide for a silicon region, said method comprising:

depositing a metal containing silicon or an alloy thereof on a bulk silicon substrate;

reacting said metal containing silicon or said alloy to form a first silicide phase;

etching any unreacted metal containing silicon or alloy;

depositing a silicon cap layer over said first silicide phase;

reacting the silicon cap layer to form a second phase; and

etching any unreacted silicon from said silicon cap layer, wherein said metal is nickel.